



# STP10NK80Z, STP10NK80ZFP, STW10NK80Z

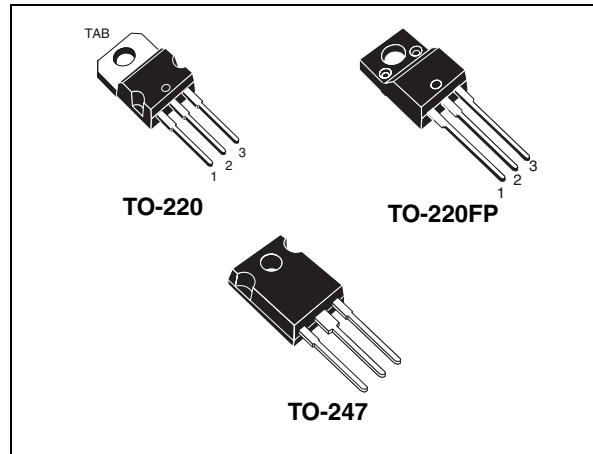
N-channel 800 V, 0.78  $\Omega$ , 9 A Zener-protected SuperMESH™ Power MOSFETs in TO-220, TO-220FP and TO-247 packages

Datasheet — production data

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>	P <sub>w</sub>
STP10NK80Z	800V	<0.90 $\Omega$	9A	160 W
STP10NK80ZFP	800V	<0.90 $\Omega$	9A	40 W
STW10NK80Z	800V	<0.90 $\Omega$	9A	160 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized
- Very low intrinsic capacitances
- Very good manufacturing repeability



## Applications

- Switching application

## Description

These devices are N-channel Zener-protected Power MOSFETs developed using STMicroelectronics' SuperMESH™ technology, achieved through optimization of ST's well established strip-based PowerMESH™ layout. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

Figure 1. Internal schematic diagram

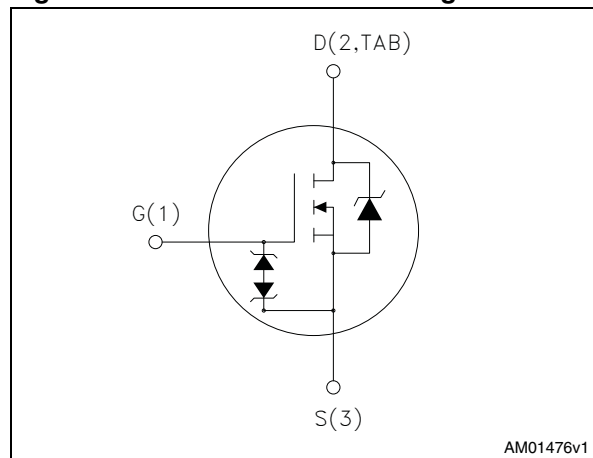


Table 1. Device summary

Part number	Marking	Package	Packaging
STP10NK80Z	P10NK80Z	TO-220	Tube
STP10NK80ZFP	P10NK80ZFP	TO-220FP	Tube
STW10NK80Z	W10NK80Z	TO-247	Tube

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220/ TO-247	TO-220FP	
$V_{DSS}$	Drain-source voltage ( $V_{GS} = 0$ )	800		V
$V_{DGR}$	Drain-gate voltage ( $R_{GS} = 20k\Omega$ )	800		V
$V_{GS}$	Gate-source voltage	$\pm 30$		V
$I_D$	Drain current (continuous) at $T_C = 25^\circ C$	9	9 <sup>(1)</sup>	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ C$	6	6 <sup>(1)</sup>	A
$I_{DM}^{(2)}$	Drain current (pulsed)	36	36 <sup>(1)</sup>	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ C$	160	40	W
	Derating factor	1.28	0.32	W/°C
Vesd(G-S)	G-S ESD (HBM C=100pF, R=1.5kΩ)	4		kV
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	4.5		V/ns
$V_{ISO}$	Insulation withstand voltage (DC)	--	2500	V
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 150		°C

- Limited by maximum junction temperature.
- Pulse width limited by safe operating area.
- $I_{SD} \leq 9$  A,  $di/dt \leq 200$  A/μs,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq T_{JMAX}$

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-247	
$R_{thj-case}$	Thermal resistance junction-case Max	0.78	3.1	0.78	°C/W
$R_{thj-a}$	Thermal resistance junction-ambient Max	62.5		50	°C/W

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AS}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_J$ Max)	9	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25^\circ C$ , $I_d = I_{AS}$ , $V_{DD} = 50V$ )	290	mJ

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1mA, V_{GS} = 0$	800			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 800V$ $V_{DS} = 800V, T_C = 125^{\circ}C$			1 50	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20V$			$\pm 10$	$\mu A$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 100\mu A$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 4.5A$		0.78	0.9	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 4.5A$	-	9.6	-	S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1 MHz, V_{GS} = 0$	-	2180 205 38	-	pF pF pF
$C_{oss eq}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0V \text{ to } 640V$	-	105	-	pF
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 640V, I_D = 9A$ $V_{GS} = 10V$ See <a href="#">Figure 20</a>	-	72 12.5 37	-	nC nC nC

1. Pulsed: pulse duration=300 $\mu s$ , duty cycle 1.5%

2.  $C_{oss eq}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD}=400\text{ V}$ , $I_D=4.5\text{ A}$ , $R_G=4.7\Omega$ , $V_{GS}=10\text{ V}$ See <a href="#">Figure 21</a>		30 20		ns ns
$t_{d(off)}$ $t_f$	Turn-off delay Time Fall time	$V_{DD}=400\text{ V}$ , $I_D=4.5\text{ A}$ , $R_G=4.7\Omega$ , $V_{GS}=10\text{ V}$ See <a href="#">Figure 21</a>		65 17		ns ns

**Table 8. Gate-source zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}^{(1)}$	Gate-source breakdown voltage	$I_{GS}=\pm 1\text{ mA}$ (open drain)	30			V

- The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

**Table 9. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		9	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		36	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=9\text{ A}$ , $V_{GS}=0$	-		1.6	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=9\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD}=45\text{ V}$ , $T_j=150^\circ\text{C}$	-	645 6.4 20		ns $\mu\text{C}$ A

- Pulse width limited by safe operating area
- Pulsed: pulse duration=300 $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

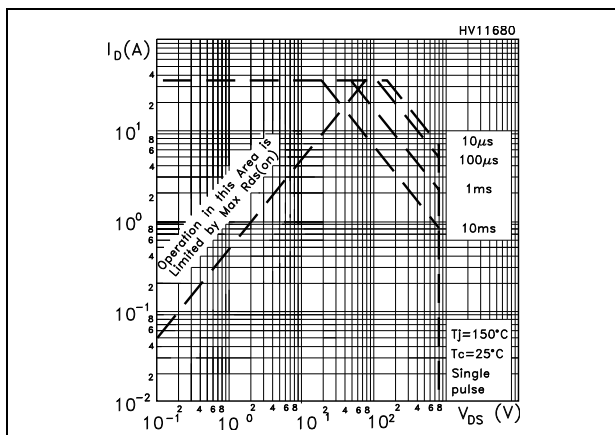


Figure 3. Thermal impedance for TO-220

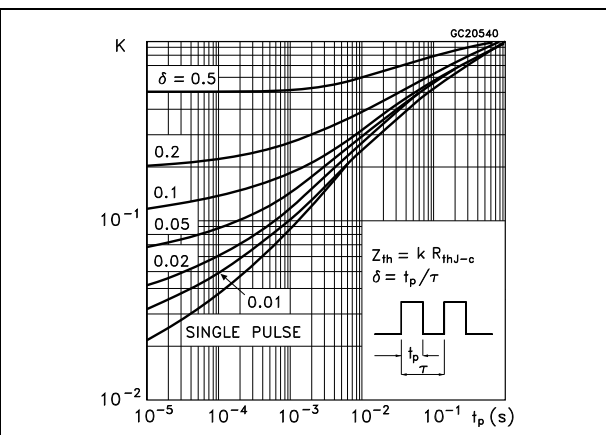


Figure 4. Safe operating area for TO-220FP

Figure 5. Thermal impedance for TO-220FP

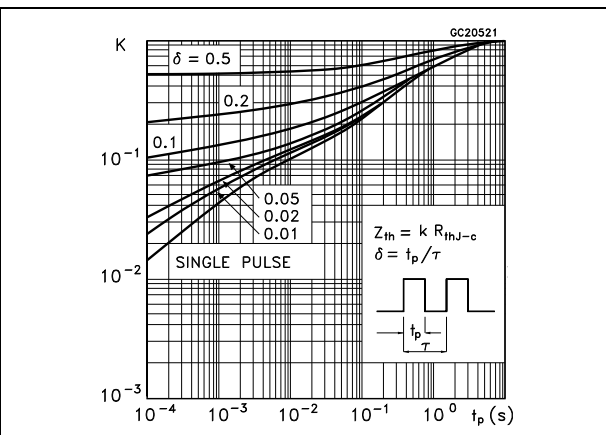
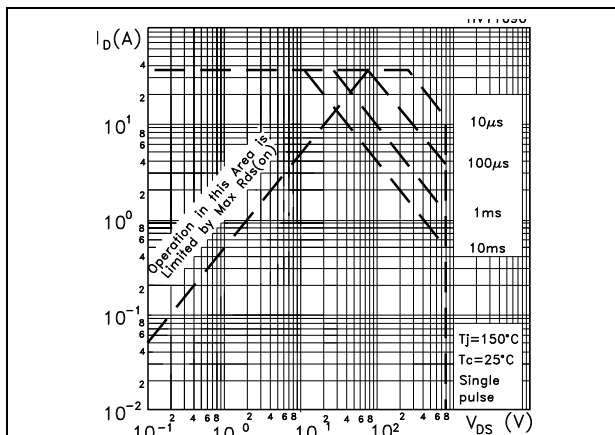


Figure 6. Safe operating area for TO-247

Figure 7. Thermal impedance for TO-247

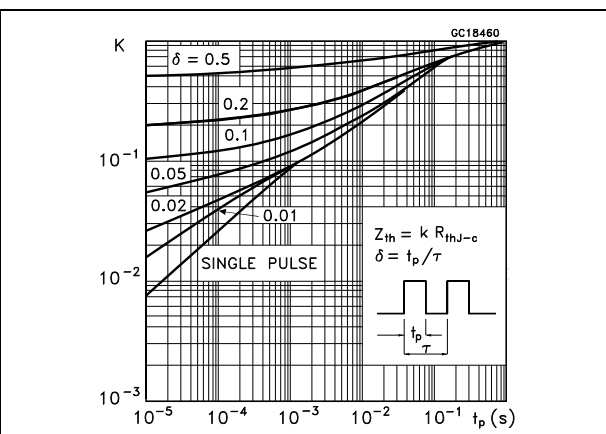
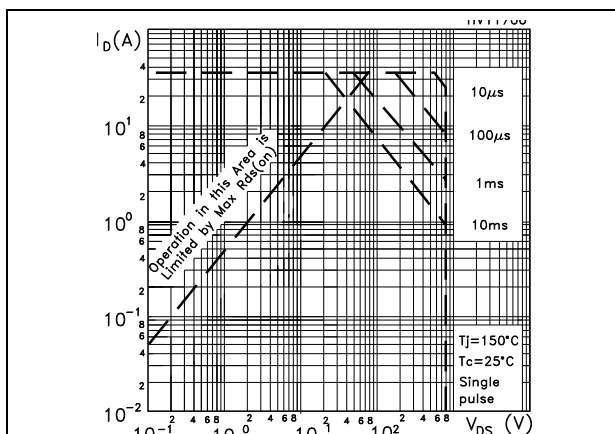


Figure 8. Output characteristics

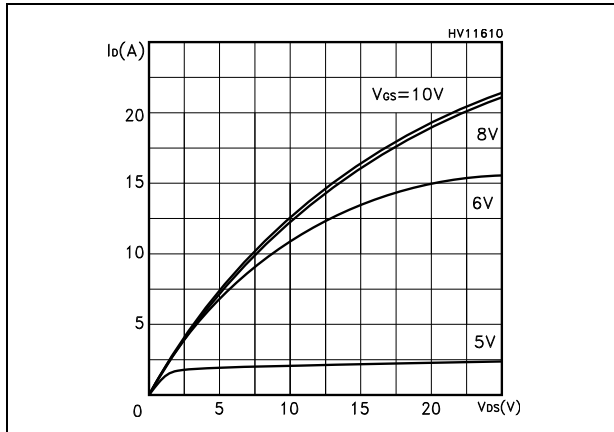


Figure 9. Transfer characteristics

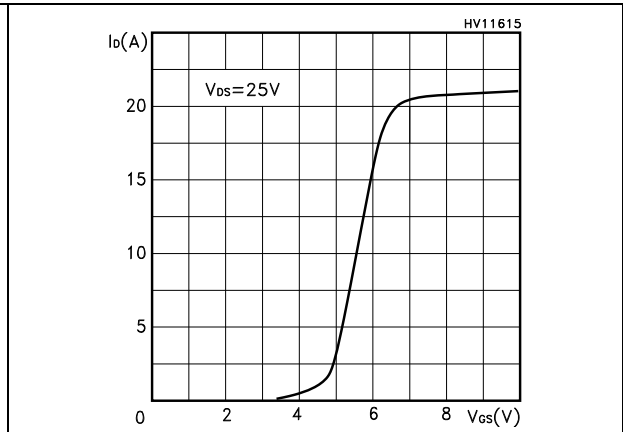


Figure 10. Transconductance

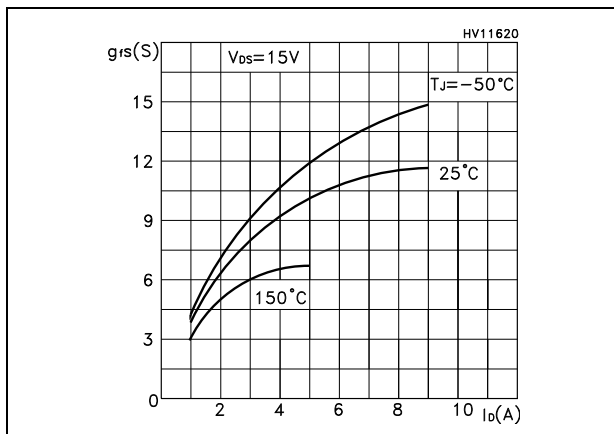


Figure 11. Static drain-source on resistance

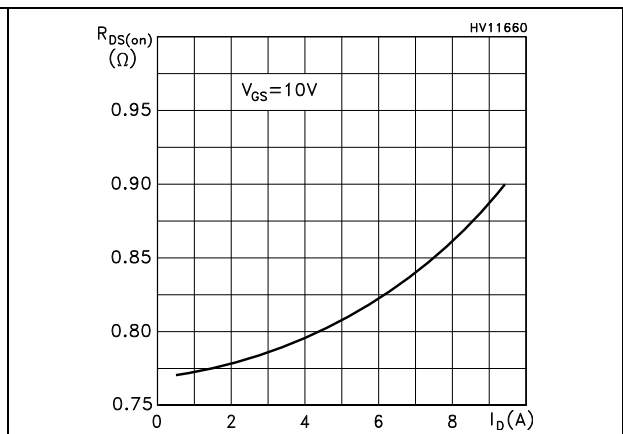


Figure 12. Gate charge vs gate-source voltage Figure 13. Capacitance variations

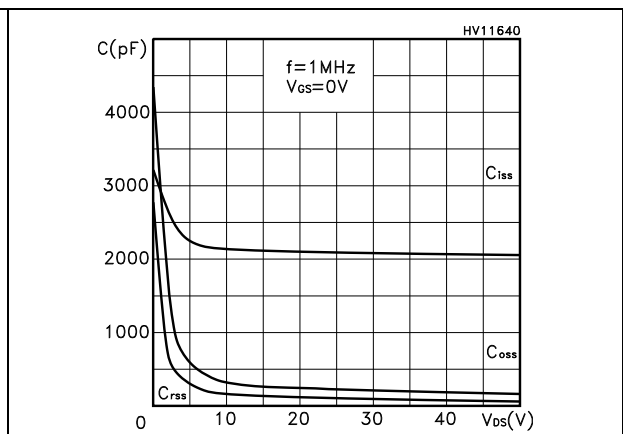
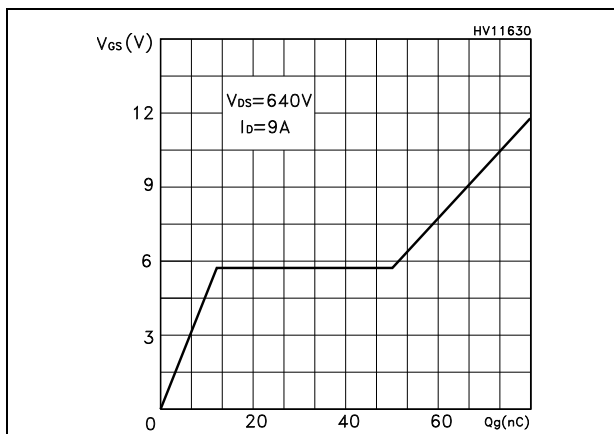


Figure 14. Normalized gate threshold voltage vs temperature

Figure 15. Normalized on resistance vs temperature

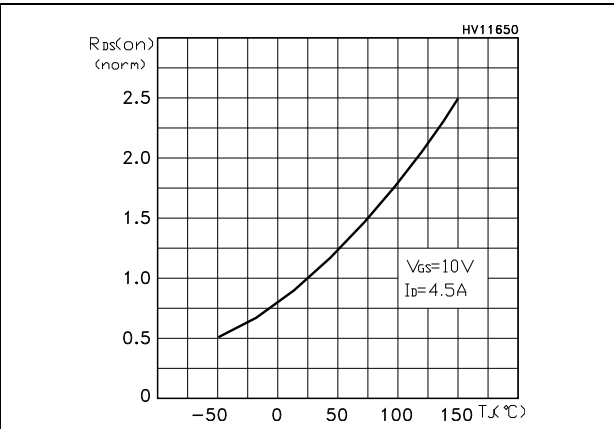
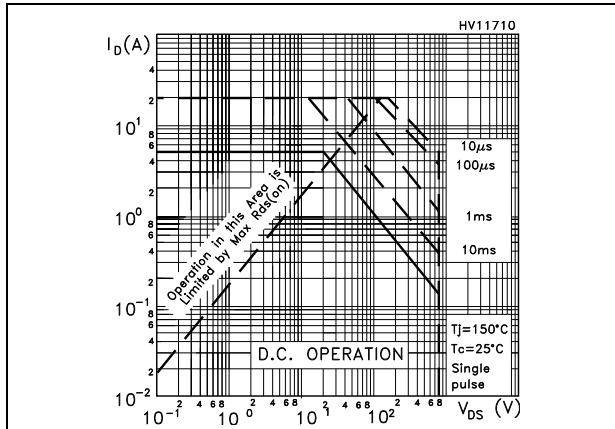


Figure 16. Source-drain diode forward characteristics

Figure 17. Normalized BV<sub>DSS</sub> vs temperature

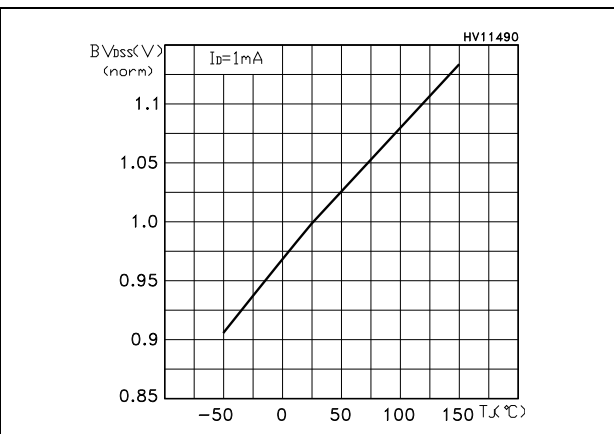
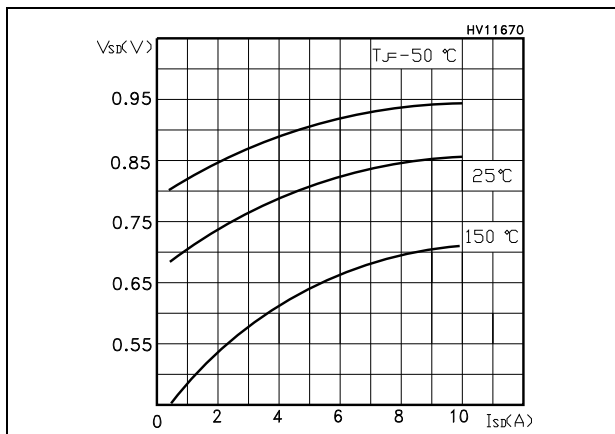
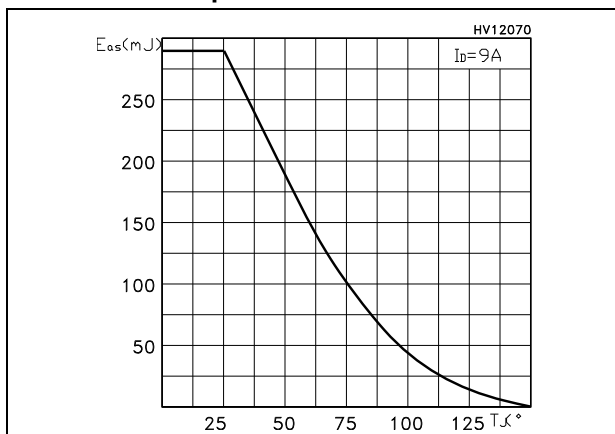


Figure 18. Maximum avalanche energy vs temperature





### 3 Test circuit

Figure 19. Switching times test circuit for resistive load

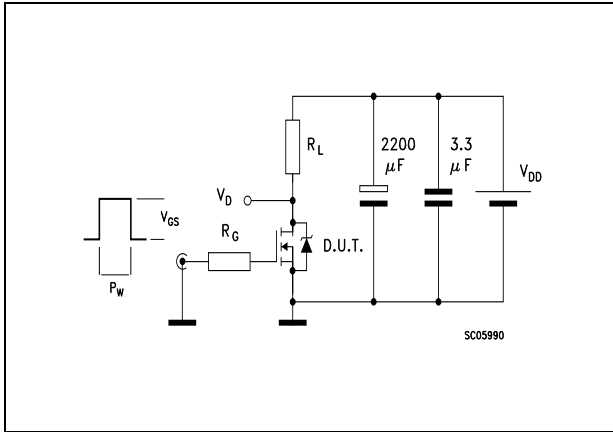


Figure 20. Gate charge test circuit

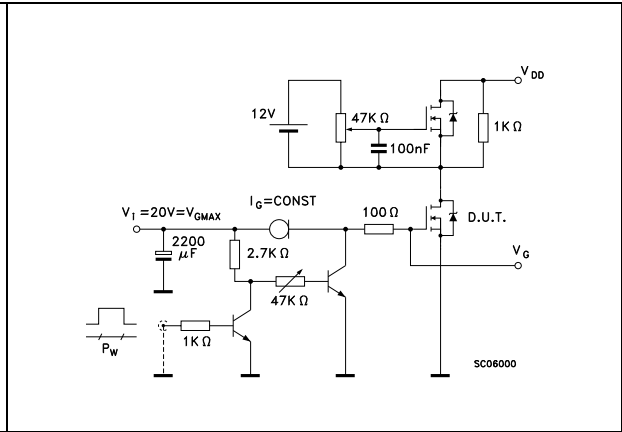


Figure 21. Test circuit for inductive load switching and diode recovery times

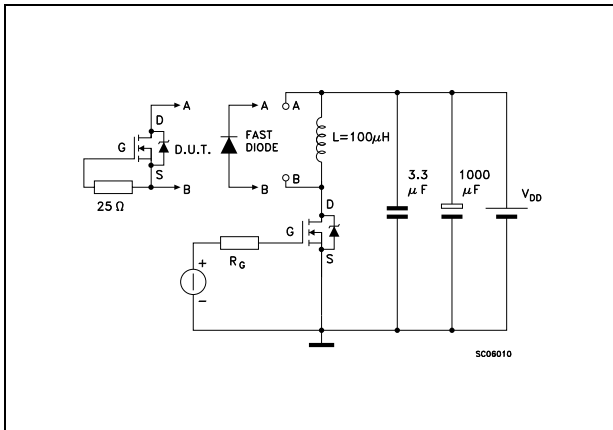


Figure 22. Unclamped Inductive load test circuit

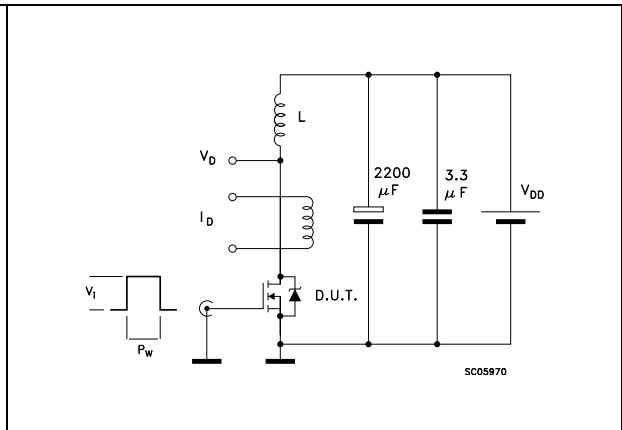


Figure 23. Unclamped inductive waveform

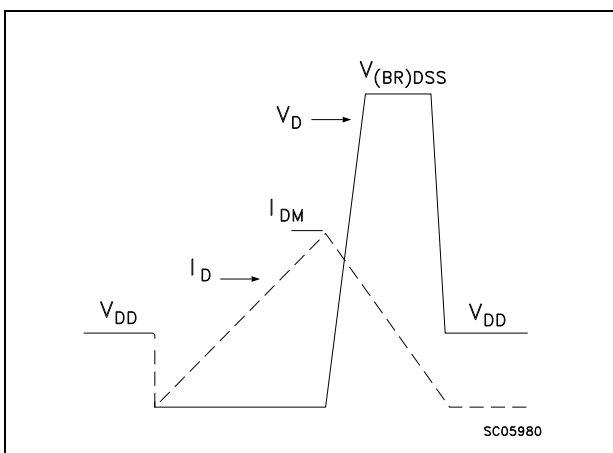
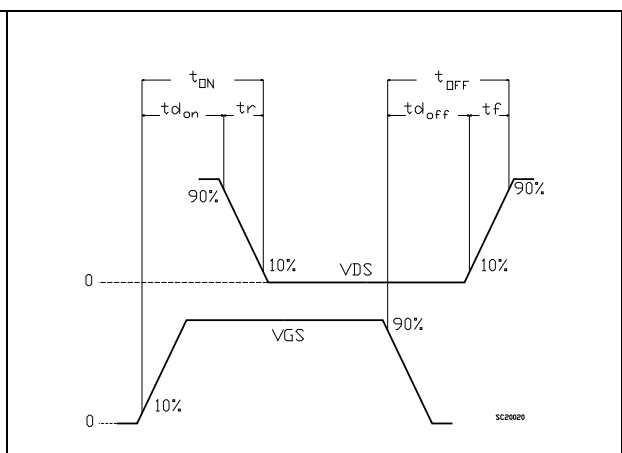


Figure 24. Switching time waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 10. TO-220 type A mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 25. TO-220 type A drawing

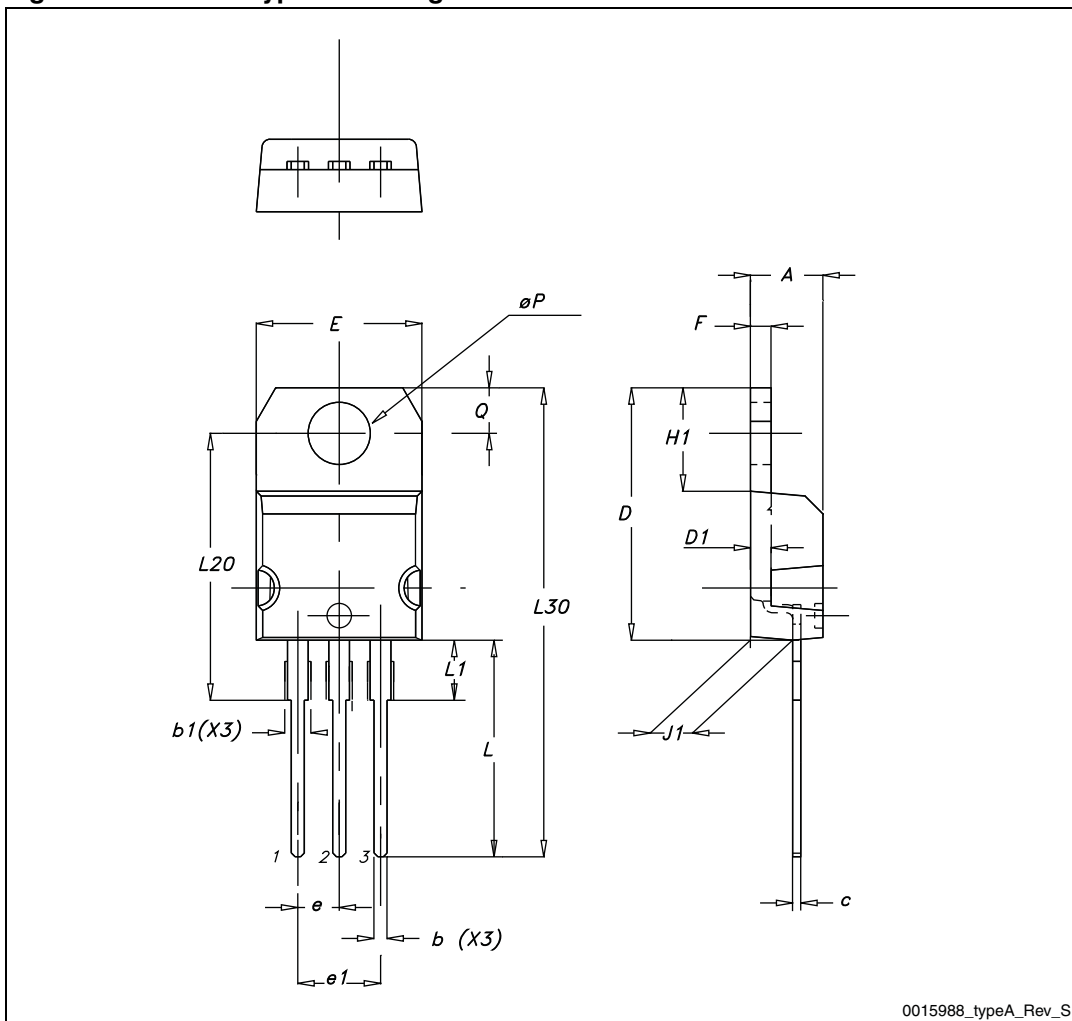


Table 11. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 26. TO-220FP drawing

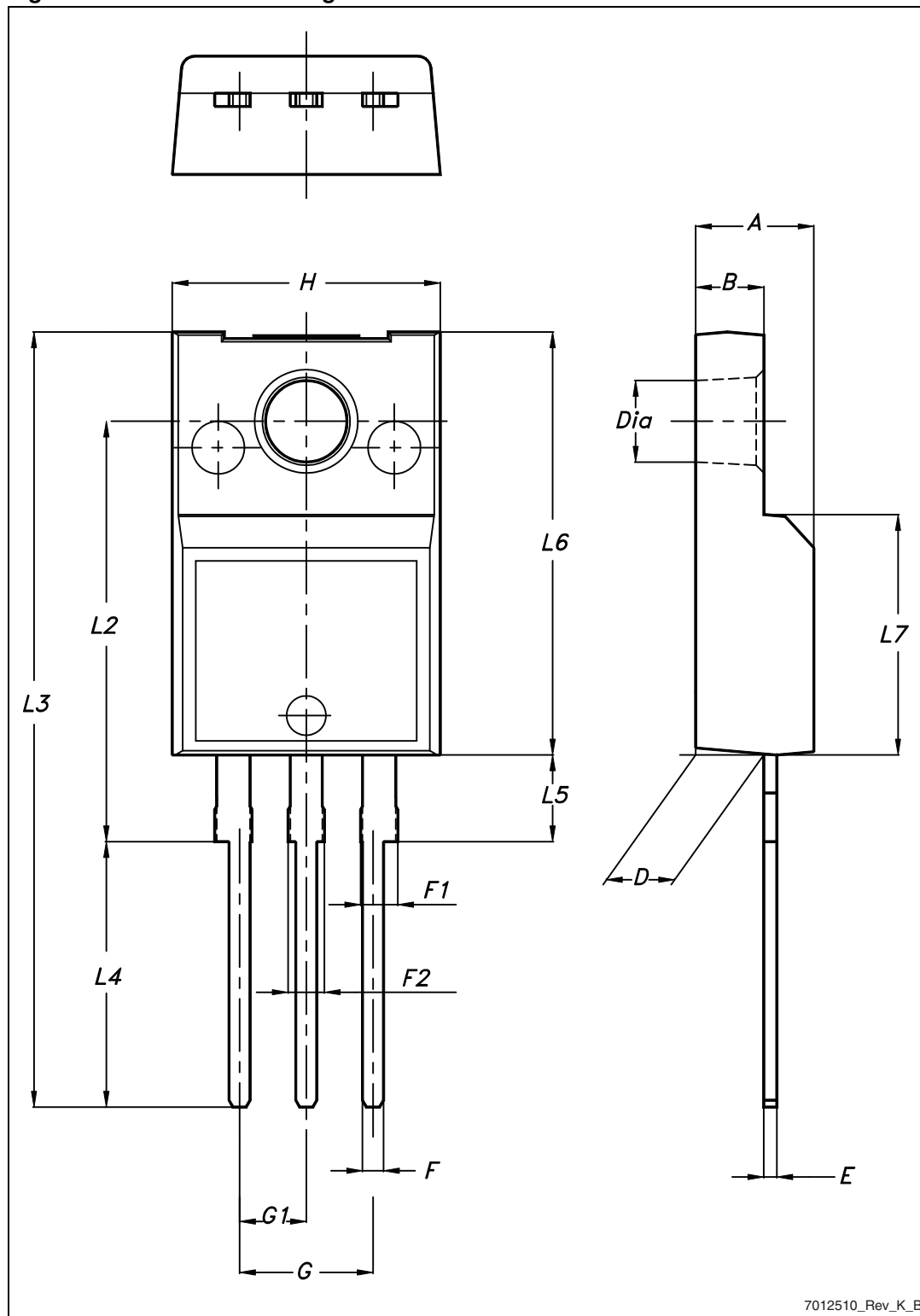
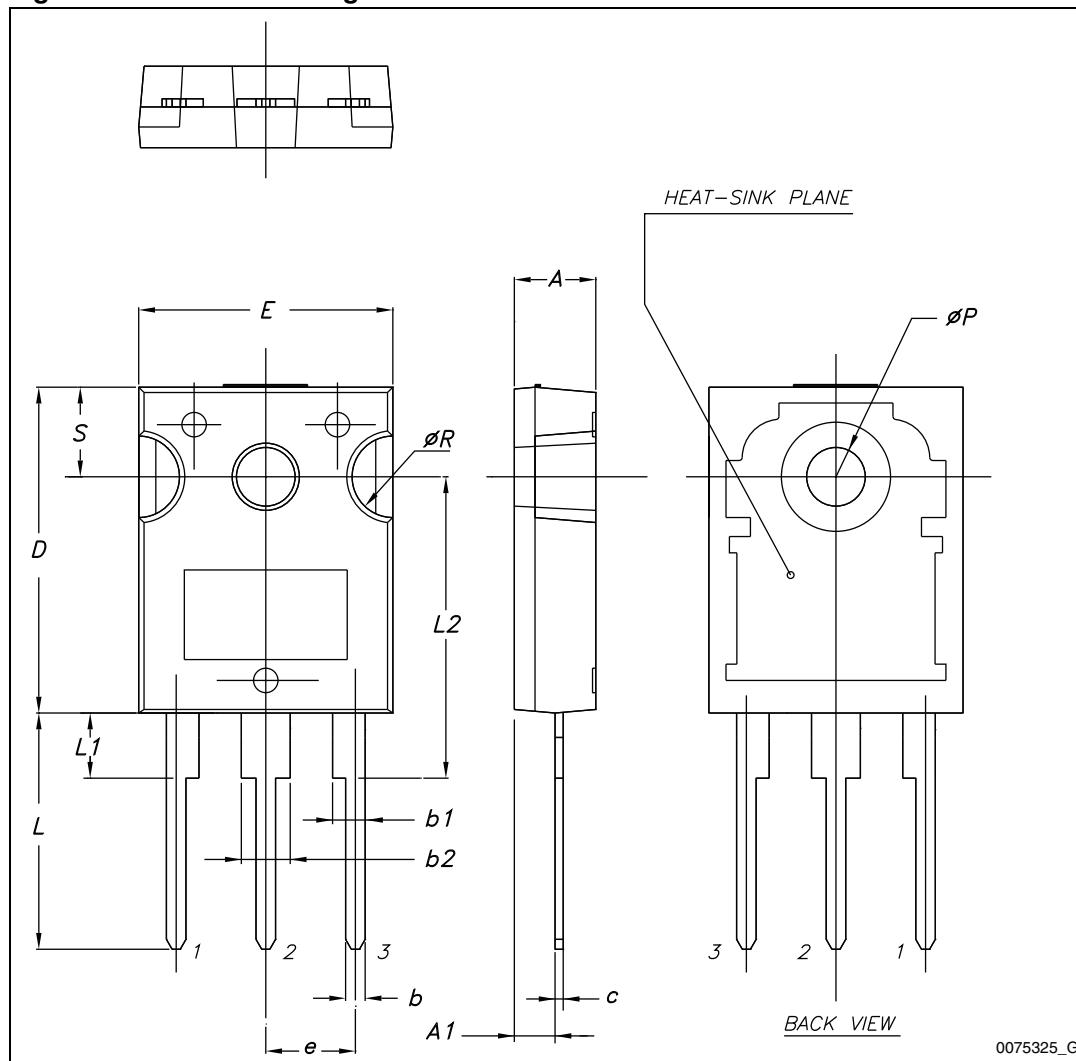


Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 27. TO-247 drawing



## 5 Revision history

**Table 13. Document revision history**

Date	Revision	Changes
08-Sep-2005	4	Complete document
10-Mar-2006	5	Inserted ecopack indication
28-Sep-2005	6	New template, no content change
15-Mar-2012	7	Content reworked to improve readability. Minor text changes in cover page. Updated <a href="#">Table 5</a> . Updated <a href="#">Section 4: Package mechanical data</a> .



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